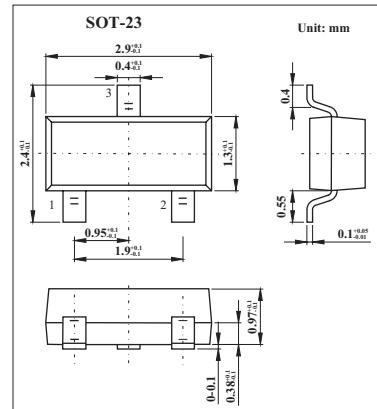


Silicon Schottky Barrier Diode

HRW0502A

■ Features

- Low forward voltage drop and suitable for high efficiency rectifying.
- MPAK package is suitable for high density surface mounting and high speed assembly.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V _{RRM}	20	V
Average rectified current	I _o	500	mA
Non-repetitive peak forward surge current	I _{FSM} (Note 1)	5	A
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55 to + 125	°C

Note

1. 10msec sine wave 1 pulse

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V _F	I _F = 500 mA			0.40	V
Reverse current	I _R	V _R = 20 V			200	µ A
Capacitance	C	V _R = 0 V, f = 1MHz		120		pF
Thermal resistance	R _{th(j-a)}	Polyimide board		340		°C/W

■ Marking

Marking	S10
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